Electrically driven surface plasmon light-emitting diodes - DTU Orbit (09/11/2017)

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We investigate device performance of GaN light-emitting diodes (LEDs) with a 30-nm p-GaN layer. The metallization used to separate the p-contact from plasmonic metals, reveals limitations on current spreading which reduces surface plasmonic enhancement.

General information

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Organisations: Department of Photonics Engineering, Diode Lasers and LED Systems, Centre of Excellence for Silicon Photonics for Optical Communications, Tokyo University of Science Authors: Fadil, A. (Intern), Ou, Y. (Intern), Iida, D. (Ekstern), Kopylov, O. (Intern), Ou, H. (Intern) Number of pages: 1 Publication date: 2016 Event: Paper presented at 4th International workshop on LEDs and solar applications, Nagoya, Japan. Main Research Area: Technical/natural sciences **Bibliographical note**

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